Docket Number: 081468-0306525 Client Reference: P-1586.010-US





Re the Application of

Group Art Unit:

beri LOF et al.

pplication No.: 10/705,816

Examiner: Unassigned

Filed: November 12, 2003

Confirmation No.: Unassigned

For: Lithographic Apparatus and Device Manufacturing Method

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. 1.56, the attention of the Patent and Trademark Office is hereby directed to the following U.S. patent application(s):

Examiner's Initials	First Inventor	Application No.	Filing Date	Enclosed
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11	Joeri LOF et al.	10/705,805	11/12/2003	☒ Specification☒ Drawings☒ Other: stamped receipt card
71	Joeri LOF et al.	10/705,783	11/12/2003	 ☒ Specification ☒ Drawings ☒ Other: stamped receipt card
71	Helmar VAN SANTEN et al.		12/23/2003	 ☑ Specification ☑ Drawings ☑ Other: stamped receipt card
TL	Johannes C.H. MULKENS et al.	10/743,266	12/23/2003	⊠ Specification ☑ Drawings ☑ Other: stamped receipt card
TL	Antonius T.A.M. DERKSEN et al.	10/705,785	11/12/2003	 ✓ Specification ✓ Drawings ✓ Other: stamped receipt card
TL	Klaus SIMON et al.	10/724,402	12/01/2003	 ✓ Specification ✓ Drawings ✓ Other: stamped receipt card
TL	Amo J. BLEEKER	10/715,116	11/18/2003	⊠ Specification ☐ Drawings ☑ Other: stamped receipt card
76	Bob STREEFKERK et al.	10/719,683	11/24/2003	☒ Specification☒ Drawings☒ Other: stamped receipt card
TL	Joannes T. DeSMIT et al.	10/705,804	11/12/2003	☑ Specification☑ Drawings☑ Other: stamped receipt card

*The Examiner's initials adjacent a citation indicates he/she has considered the cited application relative to the subject application.

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<u>PATENT APPLICATION</u>

Docket Number: 081468-0306525 Client Reference: P-1586.010-US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

e the Application of

OF et al.

Group Art Unit: 2882

Application No.: 10/705,816

Examiner: Unassigned

Filed: November 12, 2003

Confirmation No.: 5408

For: LITHOGRAPHIC APPARATUS AND DEVICE MANUFACTURING METHOD

January 7, 2005

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. 1.56, the attention of the Patent and Trademark Office is hereby directed to the following U.S. patent application(s):

Examiner's Initials	First Inventor	Application No.	Filing Date	Enclosed
TL	SUWA et al. (Reissue Application of U.S. Patent No. 6,191,429 B1)	10/367.910	02/19/2003	Specification Drawings Other: stamped receipt card
TL	HOOGENDAM et al. (081468-0308674)	10/831,370	04/26/2004	☒ Specification☒ Drawings☒ Other: stamped receipt card

^{*}The Examiner's initials adjacent a citation indicates he/she has considered the cited application relative to the subject application.

It is respectfully requested that these applications and the art cited therein during examination be expressly considered during the prosecution of this application and be made of record in this application. The identification of the above U.S. patent applications is not to be construed as a waiver of secrecy as to those applications now or upon issuance of the present application as a patent.

<u>PLEASE DO NOT PRINT</u> the above information on the patent which results from this application.

Consideration of each listed application is earnestly solicited since unpublished patent applications are contemplated as IDS material; see the exception in Rule 98(a)(2)(iii) and note the penultimate sentence of MPEP 609.

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